









SN74LVC1T45-Q1

SCES677F - SEPTEMBER 2006 - REVISED JUNE 2024

# SN74LVC1T45-Q1 Automotive 1.65V to 5.5V Single-Bit Dual-Supply Level Shifter

#### 1 Features

- Qualified for automotive applications
- AEC-Q100 qualified with the following results:
  - Device temperature grade 1: -40°C to +125°C ambient operating temperature range
  - Device HBM ESD Classification Level H2
  - Device CDM ESD Classification Level C3B
- Fully configurable dual-rail design allows each port to operate over the full 1.65V to 5.5V power-supply
- V<sub>CC</sub> isolation feature if either V<sub>CC</sub> input is at GND, both ports are in the high-impedance state
- DIR input circuit referenced to V<sub>CCA</sub>
- ±24mA output drive at 3.3V
- I<sub>off</sub> supports partial-power-down mode operation
- Maximum data rates:
  - 420Mbps (3.3V to 5V translation)
  - 210Mbps (translate to 3.3V)
  - 140Mbps (translate to 2.5V)
  - 75Mbps (translate to 1.8V)

# 2 Applications

- Head units
- ADAS cameras
- **Telematics**

## 3 Description

The SN74LVC1T45-Q1 device is a single-bit, noninverting bus transceiver that uses two separate configurable power supply rails. The A-port is designed to track V<sub>CCA</sub>. V<sub>CCA</sub> accepts any supply voltage from 1.65V to 5.5V. The B-port is designed to track V<sub>CCB</sub>. V<sub>CCB</sub> accepts any supply voltage from 1.65V to 5.5V. This allows for universal low-voltage bidirectional translation between any of the 1.8V, 2.5V, 3.3V, and 5V voltage nodes.

The SN74LVC1T45-Q1 device is a single-bit, noninverting level translator. The fully configurable dualrail design allows each port to overate over the full 1.65V to 5.5V power supply range. This device is an excellent choice for applications that need a wide bidirectional translation range.

The SN74LVC1T45-Q1 is designed so that the DIR input is powered by V<sub>CCA</sub>.

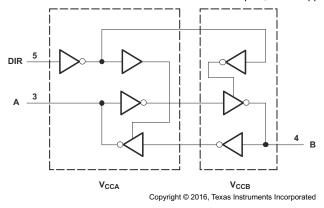
This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The V<sub>CC</sub> isolation feature is designed so that if either V<sub>CC</sub> input is at GND, then both ports are in the highimpedance state.

**Package Information** 

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
SN74LVC1T45-Q1	DCK (SC70, 6)	2mm × 2.1mm

- For more information, see Section 9
- The package size (length × width) is a nominal value and includes pins, where applicable.



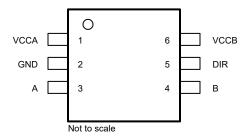
Logic Diagram (Positive Logic)



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# **4 Pin Configuration and Functions**



See mechanical drawings for dimensions.

Figure 4-1. DCK Package, 6-Pin SC70 (Top View)

**Table 4-1. Pin Functions** 

PI	N	TYPE <sup>(1)</sup>	DESCRIPTION					
NAME	NO.	I I I PE\ /	DESCRIPTION					
A 3 I/O Output level depends on V <sub>CC1</sub> voltage								
В	4	I/O	put threshold value depends on V <sub>CC2</sub> voltage					
DIR	5	I	GND (low level) determines B-port to A-port direction					
GND	2	G	Device GND					
V <sub>CCA</sub> 1 P SYSTEM-1 supply voltage (1.65V to 5.5V)		Р	SYSTEM-1 supply voltage (1.65V to 5.5V)					
V <sub>CCB</sub> 6		Р	SYSTEM-2 supply voltage (1.65V to 5.5V)					

(1) G = Ground, I = Input, O = Output, P = Power

# 5 Specifications

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage, V <sub>CCA</sub> , V <sub>CCB</sub>		-0.5	6.5	V
Input voltage, V <sub>I</sub> <sup>(2)</sup>		-0.5	6.5	V
Voltage applied to any output in the high-impedance or power-off state, Vo	o <sup>(2)</sup>	-0.5	6.5	V
Voltage applied to any output in the high or low state, $V_0^{(2)(3)}$	A port	-0.5	V <sub>CCA</sub> + 0.5	V
Voltage applied to any output in the high or low state, $v_0 \leftarrow v_0$	B port	-0.5	V <sub>CCB</sub> + 0.5	v
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)			<b>–</b> 50	mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)			<i>–</i> 50	mA
Continuous output current, I <sub>O</sub>			±50	mA
Continuous current through V <sub>CC</sub> or GND			±100	mA
Junction temperature, T <sub>J</sub>			150	°C
Storage temperature, T <sub>stg</sub>		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 3) The value of V<sub>CC</sub> is provided in *Recommended Operating Conditions*.

### 5.2 ESD Ratings

			VALUE	UNIT
\ <u>\</u>		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±750	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

## **5.3 Recommended Operating Conditions**

# See(1) (2) (3)

			MIN	MAX	UNIT
V <sub>CCA</sub>	Supply voltage		1.65	5.5	V
V <sub>CCB</sub>	Supply voltage		1.65	5.5	V
		V <sub>CCI</sub> = 1.65V to 1.95V	V <sub>CCI</sub> × 0.65		
	High-level input voltage,	V <sub>CCI</sub> = 2.3V to 2.7V	1.7		V
V <sub>IH</sub>	data inputs <sup>(4)</sup>	V <sub>CCI</sub> = 3V to 3.6V	2		V
		V <sub>CCI</sub> = 4.5V to 5.5V	V <sub>CCI</sub> × 0.7		
		V <sub>CCI</sub> = 1.65V to 1.95V		V <sub>CCI</sub> × 0.35	
,,	Low-level input voltage,	V <sub>CCI</sub> = 2.3V to 2.7V		0.7	V
V <sub>IL</sub>	data inputs <sup>(4)</sup>	V <sub>CCI</sub> = 3V to 3.6V		0.8	V
		V <sub>CCI</sub> = 4.5V to 5.5V		V <sub>CCI</sub> × 0.3	
		V <sub>CCI</sub> = 1.65V to 1.95V	V <sub>CCA</sub> × 0.65		
V	High-level input voltage,	V <sub>CCI</sub> = 2.3V to 2.7V	1.7		V
V <sub>IH</sub>	DIR (referenced to V <sub>CCA</sub> ) <sup>(5)</sup>	V <sub>CCI</sub> = 3V to 3.6V	2		V
		V <sub>CCI</sub> = 4.5V to 5.5V	V <sub>CCA</sub> × 0.7		

# **5.3 Recommended Operating Conditions (continued)**

See(1)(2)(3)

				MIN	MAX	UNIT	
			V <sub>CCI</sub> = 1.65V to 1.95V	V	<sub>CCA</sub> × 0.35		
V <sub>IL</sub>	Low-level input voltage,		V <sub>CCI</sub> = 2.3V to 2.7V		0.7	V	
VIL	DIR (referenced to V	CCA) <sup>(5)</sup>	V <sub>CCI</sub> = 3V to 3.6V		V		
			V <sub>CCI</sub> = 4.5V to 5.5V	,	V <sub>CCA</sub> × 0.3		
VI	Input voltage			0	5.5	V	
Vo	Output voltage			0	V <sub>cco</sub>	V	
	High-level output current $ \begin{array}{c} V_{CCC} \\ V_{CCC} \\ \hline V_{CCC} \end{array} $	V <sub>CCO</sub> = 1.65V to 1.95V		-4			
	High-level output current		V <sub>CCO</sub> = 2.3V to 2.7V		-8	mΛ	
Гон			V <sub>CCO</sub> = 3V to 3.6V		-24	mA	
			V <sub>CCO</sub> = 4.5V to 5.5V		-32		
			V <sub>CCO</sub> = 1.65V to 1.95V		4		
	Low lovel output our	rant	V <sub>CCO</sub> = 2.3V to 2.7V		8	mA	
I <sub>OL</sub>	Low-level output cur	rent	V <sub>CCO</sub> = 3V to 3.6V		24	ША	
			V <sub>CCO</sub> = 4.5V to 5.5V		32		
			V <sub>CCI</sub> = 1.65V to 1.95V		20		
		Dete inpute	V <sub>CCI</sub> = 2.3V to 2.7V		20		
Δt/Δv	Input transition	out transition Data inputs e or fall rate	V <sub>CCI</sub> = 3V to 3.6V		10	ns/V	
	noo or rail rate		V <sub>CCI</sub> = 4.5V to 5.5V	5			
		Control inputs, V <sub>CC</sub>	Control inputs, V <sub>CCI</sub> = 1.65V to 5.5V		5		
T <sub>A</sub>	Operating free-air te	mperature		-40	125	°C	

- (2)
- $V_{CCI}$  is the  $V_{CC}$  associated with the input port.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port. All unused data inputs of the device must be held at  $V_{CCI}$  or GND for proper device operation. See *Implications of Slow or Floating* CMOS Inputs (SCBA004).
- (4) For V<sub>CCI</sub> values not specified in the data sheet, V<sub>IH</sub> min = V<sub>CCI</sub> × 0.7V, V<sub>IL</sub> max = V<sub>CCI</sub> × 0.3V.
   (5) For V<sub>CCI</sub> values not specified in the data sheet, V<sub>IH</sub> min = V<sub>CCA</sub> × 0.7V, V<sub>IL</sub> max = V<sub>CCA</sub> × 0.3V.

### **5.4 Thermal Information**

		SN74LVC1T45-Q1	
	THERMAL METRIC(1)	DCK (SC70)	UNIT
		6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	139.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	72	°C/W
ΨЈТ	Junction-to-top characterization parameter	54.9	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	71.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	_	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

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### 5.5 Electrical Characteristics

over operating free-air temperature range with all limits at  $T_A = -40$ °C to 125°C (unless otherwise noted)<sup>(1)</sup> (2)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
		$I_{OH}$ = -100 $\mu$ A, $V_{CCA}$ = 1 $V_{CCB}$ = 1.65V to 4.5V	.65V to 4.5V,	V <sub>CCO</sub> - 0.1				
		$I_{OH} = -4mA$ , $V_{CCA} = 1.65$	I <sub>OH</sub> = -4mA, V <sub>CCA</sub> = 1.65V, V <sub>CCB</sub> = 1.65V					
V <sub>OH</sub>	$V_I = V_{IH}$	I <sub>OH</sub> = -8mA, V <sub>CCA</sub> = 2.3\	/, V <sub>CCB</sub> = 2.3V	1.9			V	
		$I_{OH} = -24$ mA, $V_{CCA} = 3$ V	, V <sub>CCB</sub> = 3V	2.3				
		$I_{OH} = -32 \text{mA}, V_{CCA} = 4.5$	5V, V <sub>CCB</sub> = 4.5V	3.8				
		I <sub>OL</sub> = 100 μA, V <sub>CCA</sub> = 1.6 V <sub>CCB</sub> = 1.65V to 4.5V	5V to 4.5V,			0.1		
		$I_{OL} = 4mA, V_{CCA} = 1.65V$	', V <sub>CCB</sub> = 1.65V			0.45		
V <sub>OL</sub>	$V_I = V_{IL}$	$I_{OL} = 8mA, V_{CCA} = 2.3V,$	V <sub>CCB</sub> = 2.3V			0.4	V	
		I <sub>OL</sub> = 24mA, V <sub>CCA</sub> = 3V, V	V <sub>CCB</sub> = 3V			0.65		
		I <sub>OL</sub> = 32mA, V <sub>CCA</sub> = 4.5V	', V <sub>CCB</sub> = 4.5V			0.65		
I.	DIR at $V_I = V_{CCA}$ or GND,	$V_{CCA}$ = 1.65V to 5.5V, $V_{CC}$	T <sub>A</sub> = 25°C			±1		
lı	= 1.65V to 5.5V		$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			±4	μA	
		A port at V <sub>CCA</sub> = 0V,	T <sub>A</sub> = 25°C			±1		
۱.,	$V_{I}$ or $V_{O} = 0$ to 5.5V	$V_{CCB} = 0$ to 5.5V	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			±10	μA	
I <sub>off</sub>	V  01 V <sub>0</sub> = 0 to 3.5V	B port at V <sub>CCA</sub> = 0	T <sub>A</sub> = 25°C	±1			μΛ	
		to 5.5V, V <sub>CCB</sub> = 0V	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			±10		
lo-	A or B port at V <sub>O</sub> = V <sub>CCO</sub> o		T <sub>A</sub> = 25°C			±1	μA	
l <sub>OZ</sub>	$V_{CCA} = 1.65V \text{ to } 5.5V, V_{CC}$	<sub>B</sub> = 1.65V to 5.5V	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			±10	μΛ	
		$V_{CCA}$ = 1.65V to 5.5V, $V_{CCA}$			10			
I <sub>CCA</sub>	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 5.5V$ , $V_{CCB} = 0V$				4		
		$V_{CCA} = 0V, V_{CCB} = 5.5V$			-10			
		$V_{CCA} = 1.65V \text{ to } 5.5V, V_{CCA}$			10			
I <sub>CCB</sub>	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 5.5V$ , $V_{CCB} = 0V$	-10			μA		
		$V_{CCA} = 0V, V_{CCB} = 5.5V$			4			
I <sub>CCA</sub> + I <sub>CCB</sub>	$V_{I} = V_{CCI}$ or GND, $I_{O} = 0$ , $V_{CCB} = 1.65V$ to 5.5V	/ <sub>CCA</sub> = 1.65V to 5.5V,				20	μΑ	
Δ1	V <sub>CCA</sub> = 3V to 5.5V,	A port at V <sub>CCA</sub> – 0.6V, DI B port = open	R at V <sub>CCA</sub> ,	50			۸	
ΔI <sub>CCA</sub>	V <sub>CCB</sub> = 3V to 5.5V	DIR at V <sub>CCA</sub> – 0.6V, B po A port at V <sub>CCA</sub> or GND	ort = open,			50	μΑ	
ΔI <sub>CCB</sub>	B port at $V_{CCB} - 0.6V$ , DIR $V_{CCB} = 3V$ to 5.5V	at GND, A port = open, V	<sub>CCA</sub> = 3V to 5.5V,			50	μA	
C <sub>i</sub>	DIR at $V_I = V_{CCA}$ or GND,	T <sub>A</sub> = 25°C, V <sub>CCA</sub> = 3.3V, V	<sub>CCB</sub> = 3.3V		2.5		pF	
C <sub>io</sub>	A or B port at $V_O = V_{CCA/B}$ $V_{CCB} = 3.3V$	or GND, T <sub>A</sub> = 25°C, V <sub>CCA</sub>	= 3.3V,		6		pF	
			V <sub>CCA</sub> = V <sub>CCB</sub> = 1.8V		3			
		A-port input,	$V_{CCA} = V_{CCB} = 2.5V$		4			
		B-port output	V <sub>CCA</sub> = V <sub>CCB</sub> = 3.3V		4			
C (3)	$C_L = 0pF,$		V <sub>CCA</sub> = V <sub>CCB</sub> = 5V		4			
C <sub>pdA</sub> <sup>(3)</sup>	f = 10MHz, $t_r = t_f = 1ns$		V <sub>CCA</sub> = V <sub>CCB</sub> = 1.8V		18		pF	
		B-port input,	$V_{CCA} = V_{CCB} = 2.5V$		19			
		A-port output	$V_{CCA} = V_{CCB} = 3.3V$	20				
			V <sub>CCA</sub> = V <sub>CCB</sub> = 5V		21			

# 5.5 Electrical Characteristics (continued)

over operating free-air temperature range with all limits at  $T_A = -40^{\circ}\text{C}$  to 125°C (unless otherwise noted)(1)(2)

PARAMETER		TEST CONDITIONS		MIN TYP	MAX	UNIT
			V <sub>CCA</sub> = V <sub>CCB</sub> = 1.8V	18		
		A-port input, B-port output	$V_{CCA} = V_{CCB} = 2.5V$	19		
			$V_{CCA} = V_{CCB} = 3.3V$	20		
C <sub>pdB</sub> (3)	$C_L = 0pF,$ f = 10MHz,		V <sub>CCA</sub> = V <sub>CCB</sub> = 5V	21		рF
O <sub>pdB</sub>	$t_r = t_f = 1$ ns		V <sub>CCA</sub> = V <sub>CCB</sub> = 1.8V	3		— pr
		B-port input,	$V_{CCA} = V_{CCB} = 2.5V$	4		
	A-p	A-port output	$V_{CCA} = V_{CCB} = 3.3V$	4		
			V <sub>CCA</sub> = V <sub>CCB</sub> = 5V	4		

- $\rm V_{CCO}$  is the  $\rm V_{CC}$  associated with the output port.  $\rm V_{CCI}$  is the  $\rm V_{CC}$  associated with the input port. (1)
- (3) Power dissipation capacitance per transceiver

# 5.6 Switching Characteristics: V<sub>CCA</sub> = 1.8V ±0.15V

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CCB</sub> = ±0.15		V <sub>CCB</sub> = ±0.2		V <sub>CCB</sub> = ±0.3		V <sub>CCB</sub> = ±0.5		UNIT	
	(INPUT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t <sub>PLH</sub>	А	В	3	20.7	2.2	13.3	1.7	11.3	1.4	10.2	ns	
t <sub>PHL</sub>		В	2.8	17.3	2.2	11.5	1.8	10.1	1.7	10	115	
t <sub>PLH</sub>	В	А	3	20.7	2.3	19	2.1	18.5	1.9	18.1	no	
t <sub>PHL</sub>	j B	Ь	_ ^	2.8	17.3	2.1	15.9	2	15.6	1.8	15.2	ns
t <sub>PHZ</sub>	DIR	А	5.2	22.7	4.8	21.5	4.7	21.4	5.1	20.1	no	
t <sub>PLZ</sub>	DIK	_ ^	2.3	13.5	2.1	13.5	2.4	13.7	3.1	13.9	ns	
t <sub>PHZ</sub>	DIR	В	5.2	27.9	4.9	14.5	3.6	13.3	2.3	11.2	ns	
t <sub>PLZ</sub>	DIK	В	4.2	19	2.2	12.2	2.3	11.4	2	9.4	115	
t <sub>PZH</sub> (1)	DIR	А		39.7		31.2		29.9		27.5	no	
t <sub>PZL</sub> <sup>(1)</sup>	DIK	_ ^		45.2		30.4		28.9		26.4	ns	
t <sub>PZH</sub> <sup>(1)</sup>	DID	В		34.2		26.8		25		24.1	ne	
t <sub>PZL</sub> <sup>(1)</sup>	DIR	ь		40.7		33		31.5		30.1	ns	

<sup>(1)</sup> The enable time is a calculated value, derived using the formula shown in Section 7.1.1.

# 5.7 Switching Characteristics: V<sub>CCA</sub> = 2.5V ±0.2V

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	PARAMETER FROM (INPUT)		TO (OUTPUT)	V <sub>CCB</sub> = ±0.15		V <sub>CCB</sub> = ±0.2		V <sub>CCB</sub> = ±0.3		V <sub>CCB</sub> = ±0.5		UNIT
		(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t <sub>PLH</sub>	А	В	2.3	19	1.5	11.5	1.3	9.4	1.1	8.1	ns	
t <sub>PHL</sub>		6	2.1	15.9	1.4	10.5	1.3	8.4	0.9	7.6	115	
t <sub>PLH</sub>	В	А	2.2	13.3	1.5	11.5	1.4	11	1	10.5	20	
t <sub>PHL</sub>			2.2	11.5	1.4	10.7	1.3	10	0.9	9.2	ns	
t <sub>PHZ</sub>	DIR	А	3	11.1	3.1	11.1	2.8	11.1	3.2	11.1	ns	
t <sub>PLZ</sub>	DIR		1.3	8.9	1.3	8.9	1.3	8.9	1	8.8	115	
t <sub>PHZ</sub>	DIR	В	5.2	26.7	4.1	14.4	3.9	13.2	2.4	10.1	20	
t <sub>PLZ</sub>	DIK		3.9	21.9	3.2	12.6	2.8	11.4	1.8	8.3	ns	

Product Folder Links: SN74LVC1T45-Q1

# 5.7 Switching Characteristics: V<sub>CCA</sub> = 2.5V ±0.2V (continued)

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CCB</sub> = 1.8V ±0.15V	V <sub>CCB</sub> = 2.5V ±0.2V	V <sub>CCB</sub> = 3.3V ±0.3V	V <sub>CCB</sub> = 5V ±0.5V	UNIT
	(INPOT)	(001701)	MIN MAX	MIN MAX	MIN MAX	MIN MAX	
t <sub>PZH</sub> (1)	DIR	А	35.2	24.1	22.4	18.8	ns
t <sub>PZL</sub> (1)	DIK		38.2	24.9	23.2	19.3	115
t <sub>PZH</sub> <sup>(1)</sup>	DIR	В	27.9	20.4	18.3	16.9	ne
t <sub>PZL</sub> <sup>(1)</sup>	DIK	В	27	21.6	19.5	18.7	ns

# 5.8 Switching Characteristics: $V_{CCA} = 3.3V \pm 0.3V$

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CCB</sub> = ±0.15		V <sub>CCB</sub> = ±0.2		V <sub>CCB</sub> = ±0.3		V <sub>CCB</sub> = ±0.5		UNIT
	(INPOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>PLH</sub>	Α	В	2.1	18.5	1.4	11	0.7	8.8	0.7	7.4	ns
t <sub>PHL</sub>			2	15.6	1.3	10	0.8	8	0.7	7	115
t <sub>PLH</sub>	В	А	1.7	11.3	1.3	9.4	0.7	8.8	0.6	8.4	ns
t <sub>PHL</sub>	В		1.8	10.1	1.3	8.4	0.8	8	0.7	7.5	115
t <sub>PHZ</sub>	DIR	A	2.9	10.3	3	10.3	2.8	10.3	3.4	10.3	10.3 8.7
t <sub>PLZ</sub>	DIK		1.8	8.6	1.6	8.6	2.2	8.7	2.2	8.7	
t <sub>PHZ</sub>	DIR	В	5.4	27.5	3.9	13.1	2.9	11.8	2.4	9.8	ns
$t_{PLZ}$	DIK		3.3	17.5	2.9	10.8	2.4	10.1	1.7	7.9	115
t <sub>PZH</sub> (1)	DIR	A		26.8		20.2		18.9		16.3	ne
t <sub>PZL</sub> <sup>(1)</sup>	DIIX			37.6		21.5		19.8		17.3	ns
t <sub>PZH</sub> (1)	DIR	В		27.1		19.6		17.5		16.1	ne
t <sub>PZL</sub> (1)	DIIX			25.9		20.3		18.3		17.3	ns

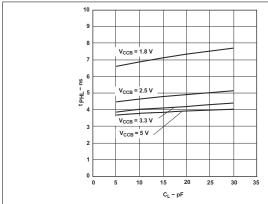
# 5.9 Switching Characteristics: $V_{CCA} = 5V \pm 0.5V$

over operating free-air temperature range (unless otherwise noted; see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CCB</sub> = ±0.15		V <sub>CCB</sub> = ±0.2		V <sub>CCB</sub> = ±0.3		V <sub>CCB</sub> = ±0.5		UNIT
	(IIII OT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>PLH</sub>	А	В	1.9	18.1	1	10.5	0.6	8.4	0.5	6.9	ne
t <sub>PHL</sub>	A	В	1.8	15.2	0.9	9.2	0.7	7.5	0.5	6.5	ns
t <sub>PLH</sub>	В	А	1.4	10.2	1	8.1	0.7	7.4	0.5	6.9	ns
t <sub>PHL</sub>	В	_ ^	1.7	10	0.9	7.6	0.7	7	0.5	6.5	
t <sub>PHZ</sub>	DIR	А	2.1	8.4	2.2	8.4	2.2	8.5	2.2	8.4	6.7 ns
t <sub>PLZ</sub>	DIK	_ ^	0.9	6.8	1	6.8	0.7	6.7	0.7	6.7	
t <sub>PHZ</sub>	DIR	В	4.8	26.2	2.5	14.8	1	11.5	2.5	9.5	ns
t <sub>PLZ</sub>	DIK	В	3.2	17.8	2.5	10.4	2.5	10	1.6	7.5	115
t <sub>PZH</sub> (1)	DIR	А		28		18.5		17.4		14.4	20
t <sub>PZL</sub> (1)	DIK			36.2		22.4		18.5		16	ns
t <sub>PZH</sub> (1)	DIR	В		24.9		17.3		15.1		13.6	20
t <sub>PZL</sub> <sup>(1)</sup>	אוע	ם		23.6		17.6		16		14.9	ns

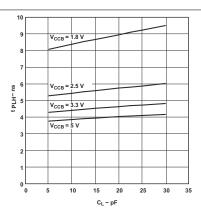


# 5.10 Typical Characteristics



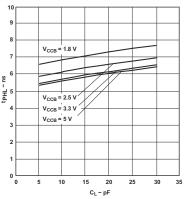
 $T_A = 25^{\circ}C, V_{CCA} = 1.8V$ 

Figure 5-1. Typical Propagation Delay (A to B) vs Load Capacitance



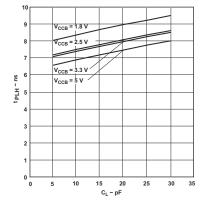
 $T_A = 25$ °C,  $V_{CCA} = 1.8V$ 

Figure 5-2. Typical Propagation Delay (A to B) vs Load Capacitance



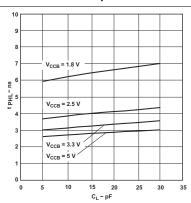
 $T_A = 25^{\circ}C, V_{CCA} = 1.8V$ 

Figure 5-3. Typical Propagation Delay (B to A) vs Load Capacitance



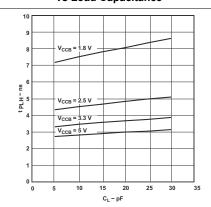
 $T_A = 25^{\circ}C, V_{CCA} = 1.8V$ 

Figure 5-4. Typical Propagation Delay (B to A) vs Load Capacitance



 $T_A = 25^{\circ}C, V_{CCA} = 2.5V$ 

Figure 5-5. Typical Propagation Delay (A to B) vs Load Capacitance

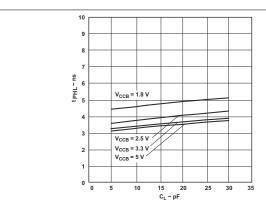


 $T_A = 25^{\circ}C, V_{CCA} = 2.5V$ 

Figure 5-6. Typical Propagation Delay (A to B) vs Load Capacitance

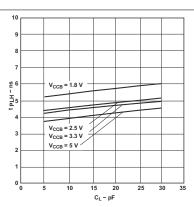


# **5.10 Typical Characteristics (continued)**



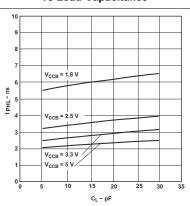
 $T_A = 25^{\circ}C, V_{CCA} = 2.5V$ 

Figure 5-7. Typical Propagation Delay (B to A) vs Load Capacitance



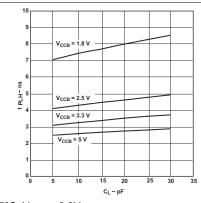
 $T_A = 25^{\circ}C, V_{CCA} = 2.5V$ 

Figure 5-8. Typical Propagation Delay (B to A) vs Load Capacitance



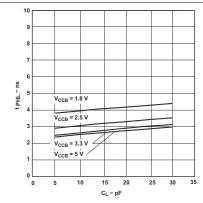
 $T_A = 25^{\circ}C, V_{CCA} = 3.3V$ 

Figure 5-9. Typical Propagation Delay (A to B)
vs Load Capacitance



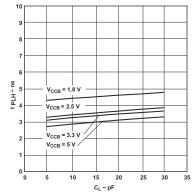
$$T_A = 25^{\circ}C, V_{CCA} = 3.3V$$

Figure 5-10. Typical Propagation Delay (A to B) vs Load Capacitance



 $T_A = 25^{\circ}C, V_{CCA} = 3.3V$ 

Figure 5-11. Typical Propagation Delay (B to A) vs Load Capacitance

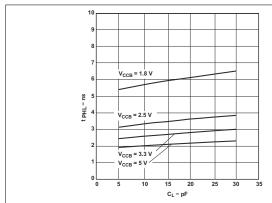


 $T_A = 25^{\circ}C, V_{CCA} = 3.3V$ 

Figure 5-12. Typical Propagation Delay (B to A) vs Load Capacitance

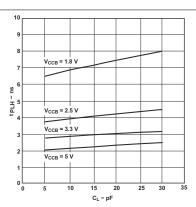


# **5.10 Typical Characteristics (continued)**



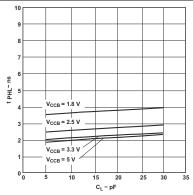
 $T_A = 25$ °C,  $V_{CCA} = 5V$ 

Figure 5-13. Typical Propagation Delay (A to B) vs Load Capacitance



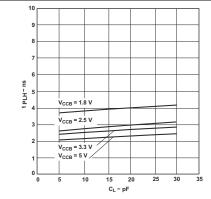
 $T_A = 25$ °C,  $V_{CCA} = 5V$ 

Figure 5-14. Typical Propagation Delay (A to B) vs Load Capacitance



 $T_A = 25$ °C,  $V_{CCA} = 5V$ 

Figure 5-15. Typical Propagation Delay (B to A) vs Load Capacitance



 $T_A = 25$ °C,  $V_{CCA} = 5V$ 

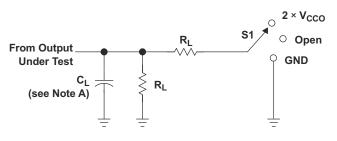
Figure 5-16. Typical Propagation Delay (B to A) vs Load Capacitance

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 $\mathbf{V}_{\mathsf{CCA}}$ 

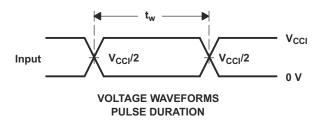
### **Parameter Measurement Information**



TEST	S1
t <sub>pd</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	2 × V <sub>CCO</sub>
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

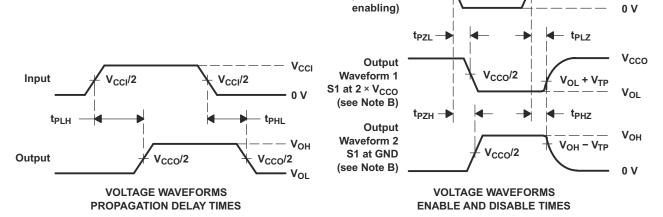
**LOAD CIRCUIT** 

V <sub>CCO</sub>	CL	$R_L$	V <sub>TP</sub>
1.8 V ± 0.15 V	15 pF	<b>2 k</b> Ω	0.15 V
2.5 V ± 0.2 V	15 pF	<b>2 k</b> Ω	0.15 V
3.3 V ± 0.3 V	15 pF	<b>2 k</b> Ω	0.3 V
5 V ± 0.5 V	15 pF	<b>2 k</b> Ω	0.3 V



V<sub>CCA</sub>/2

V<sub>CCA</sub>/2



Output Control

(low-level

- NOTES: A. C<sub>I</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_0 = 50 \Omega$ ,  $dv/dt \geq$  1 V/ns.
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E. t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as t<sub>dis</sub>.
  - F.  $\,t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}.$
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
  - H.  $V_{CCI}$  is the  $V_{CC}$  associated with the input port.
  - I.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port.
  - J. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

# **6 Detailed Description**

### 6.1 Overview

The SN74LVC1T45-Q1 is single-bit, dual-supply, non-inverting voltage level translation. Pin A and that direction control pin (DIR) are supported by  $V_{CCA}$  and pin B is supported by  $V_{CCB}$ . The A port can accept I/O voltages ranging from 1.65V to 5.5V, while the B port can accept I/O voltages from 1.65V to 5.5V. The high on the DIR allows data transmissions from A to B and a low on the DIR allows data transmissions from B to A.

## 6.2 Functional Block Diagram

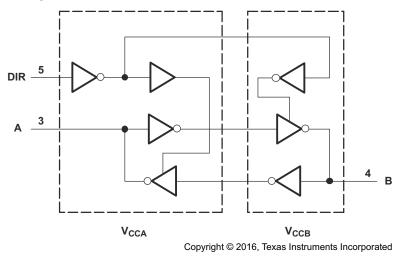


Figure 6-1. Logic Diagram (Positive Logic)

#### **6.3 Feature Description**

The SN74LVC1T45-Q1 has a fully configurable dual-rail design that allows each port to operate over the full 1.65V to 5.5V power-supply range. Both  $V_{CCA}$  and  $V_{CCB}$  can be supplied at any voltage between 1.65V and 5.5V, making the device suitable for translating between any of the voltage nodes (1.8V, 2.5V, 3.3V, and 5V).

SN74LVC1T45-Q1 can support high data rate applications. The translated signal data rate can be up to 420Mbps when the signal is translated from 3.3V to 5V.

I<sub>off</sub> prevents backflow current by disabling I/O output circuits when device is in partial-power-down mode.

#### 6.3.1 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to VCC when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

### **6.4 Device Functional Modes**

Table 6-1 lists the operational modes of SN74LVC1T45-Q1.

Table 6-1. Function Table<sup>(1)</sup>

INPUT DIR	OPERATION
L	B data to A bus
Н	A data to B bus

(1) Input circuits of the data I/Os always are active.

# **Application and Implementation**

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

# 1 Application Information

The SN74LVC1T45-Q1 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum data rate can be up to 420Mbps when device translates signals from 3.3V to 5V.

#### 1.1 Enable Times

Calculate the enable times for the SN74LVC1T45-Q1 using the following formulas:

- $t_{PZH}$  (DIR to A) =  $t_{PLZ}$  (DIR to B) +  $t_{PLH}$  (B to A)
- $t_{PZL}$  (DIR to A) =  $t_{PHZ}$  (DIR to B) +  $t_{PHL}$  (B to A)
- $t_{PZH}$  (DIR to B) =  $t_{PLZ}$  (DIR to A) +  $t_{PLH}$  (A to B)
- $t_{PZL}$  (DIR to B) =  $t_{PHZ}$  (DIR to A) +  $t_{PHL}$  (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74LVC1T45-Q1 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

## 2 Typical Applications

#### 2.1 Unidirectional Logic Level-Shifting Application

Figure 7-1 shows an example of the SN74LVC1T45-Q1 being used in a unidirectional logic level-shifting application.

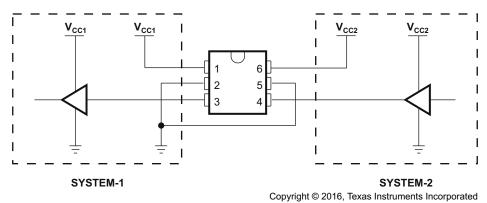


Figure 7-1. Unidirectional Logic Level-Shifting Application

### 2.1.1 Design Requirements

For this design example, use the parameters listed in Table 7-1.

Table 7-1. Design Parameters

idbic / i. bcsi	gir i didilictors
PARAMETER	VALUE
Input voltage	1.65V to 5.5V
Output voltage	1.65V to 5.5V

#### 2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the SN74LVC1T45-Q1 device to determine the input voltage range. For a valid logic high the value must exceed the VIH of the input port. For a valid logic low the value must be less than the VIL of the input port.
- Output voltage range
  - Use the supply voltage of the device that the SN74LVC1T45-Q1 device is driving to determine the output voltage range.

#### 2.1.3 Application Curves

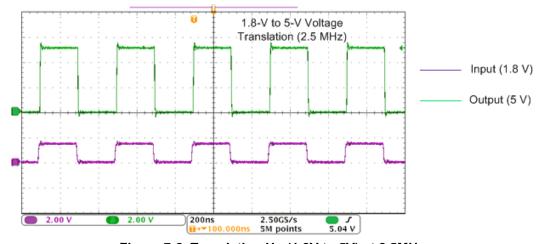


Figure 7-2. Translation Up (1.8V to 5V) at 2.5MHz

### 2.2 Bidirectional Logic Level-Shifting Application

Figure 7-3 shows the SN74LVC1T45-Q1 being used in a bidirectional logic level-shifting application. Because the SN74LVC1T45-Q1 does not have an output-enable (OE) pin, the system designer should take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.

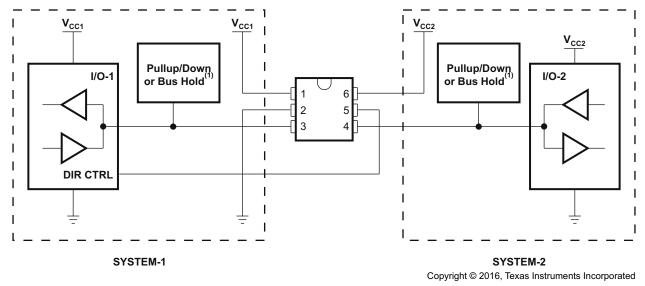


Figure 7-3. Bidirectional Logic Level-Shifting Application

Product Folder Links: SN74LVC1T45-Q1

#### 2.2.1 Detailed Design Procedure

Table 7-2 shows data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

Table	e 7-2	Data	Trans	mission

STATE	DIR CTRL	I/O-1	I/O-2	DESCRIPTION
1	Н	Out	In	SYSTEM-1 data to SYSTEM-2
2	Н	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on pullup or pulldown. <sup>(1)</sup>
3	L	Hi-Z	Hi-Z	DIR bit is flipped. I/O-1 and I/O-2 still are disabled. The bus-line state depends on pullup or pulldown. <sup>(1)</sup>
4	L	Out	In	SYSTEM-2 data to SYSTEM-1

(1) SYSTEM-1 and SYSTEM-2 must use the same conditions, that is, both pullup or both pulldown.

#### 2.2.2 Application Curves

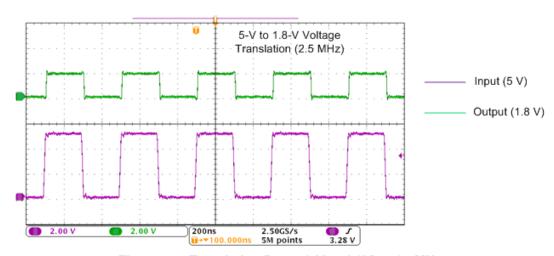


Figure 7-4. Translation Down (5V to 1.8V) at 2.5MHz

### 3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices, as described in *Glitch-free Power Supply Sequencing*.

## 4 Layout

# 4.1 Layout Guidelines

For device reliability, the following common printed-circuit board layout guidelines are recommended:

- Bypass capacitors must be used on power supplies.
- Short trace lengths must be used to avoid excessive loading.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depends on the system requirements.

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# 4.2 Layout Example



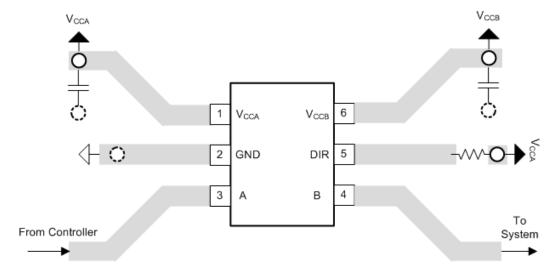


Figure 7-5. Layout Schematic

# 7 Device and Documentation Support

### 7.1 Documentation Support

#### 7.1.1 Related Documentation

For related documentation see the following:

Texas Instruments, Implications of Slow or Floating CMOS Inputs application note

### 7.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

# 7.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 7.4 Trademarks

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### 7.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 7.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

### 8 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	nanges from Revision E (December 2022) to Revision F (June 2024)	Page
•	Updated Package Information table to include package lead size	1
•	Updated the Power Supply Recommendations section	15
С	hanges from Revision D (July 2017) to Revision E (December 2022)	Page
_	hanges from Revision D (July 2017) to Revision E (December 2022)  Updated the numbering format for tables, figures, and cross-references throughout the document	
•		1

## 9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 11-Apr-2024

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1T45QDCKRQ1	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	5TR	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF SN74LVC1T45-Q1:

# **PACKAGE OPTION ADDENDUM**

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● Catalog : SN74LVC1T45

● Enhanced Product : SN74LVC1T45-EP

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

• Enhanced Product - Supports Defense, Aerospace and Medical Applications

# **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	_	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1T45QDCKRQ1	SC70	DCK	6	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3

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### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74LVC1T45QDCKRQ1	SC70	DCK	6	3000	202.0	201.0	28.0	



SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

  4. Falls within JEDEC MO-203 variation AB.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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